

# NLAS44599

## Low Voltage Single Supply Dual DPDT Analog Switch

The NLAS44599 is an advanced dual-independent CMOS double pole-double throw (DPDT) analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining CMOS low power dissipation. This DPDT controls analog and digital voltages that may vary across the full power-supply range (from  $V_{CC}$  to GND).

The device has been designed so the ON resistance ( $R_{ON}$ ) is much lower and more linear over input voltage than  $R_{ON}$  of typical CMOS analog switches.

The channel select input is compatible with standard CMOS outputs.

The channel select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The NLAS44599 can also be used as a quad 2-to-1 multiplexer-demultiplexer analog switch with two Select pins that each controls two multiplexer-demultiplexers.

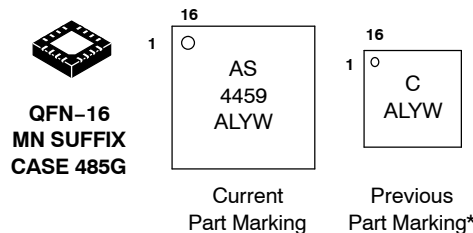
- Channel Select Input Over-Voltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break-Before-Make Circuitry
- Low Power Dissipation:  $I_{CC} = 2 \mu\text{A}$  (Max) at  $T_A = 25^\circ\text{C}$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- ESD Performance: Human Body Model; > 2000 V,  
Machine Model; > 200 V
- Chip Complexity: 158 FETs
- Pb-Free Packages are Available



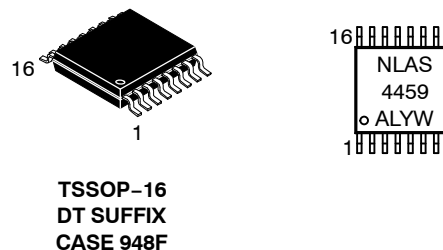
ON Semiconductor®

<http://onsemi.com>

### MARKING DIAGRAMS



\*Previous releases of this device may be marked as shown in this diagram.

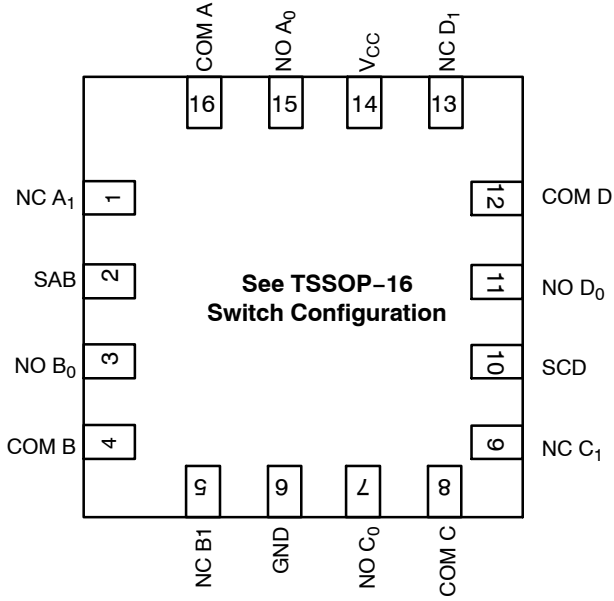


A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

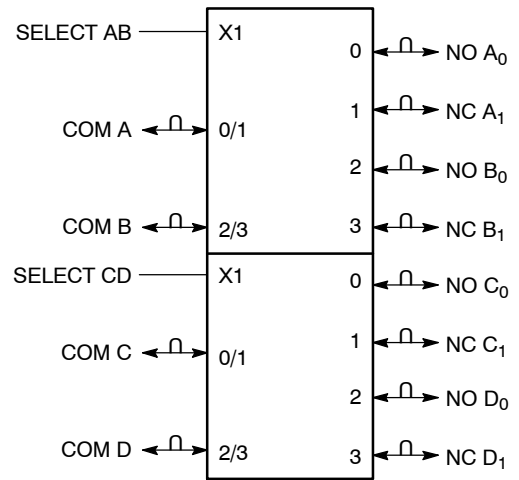
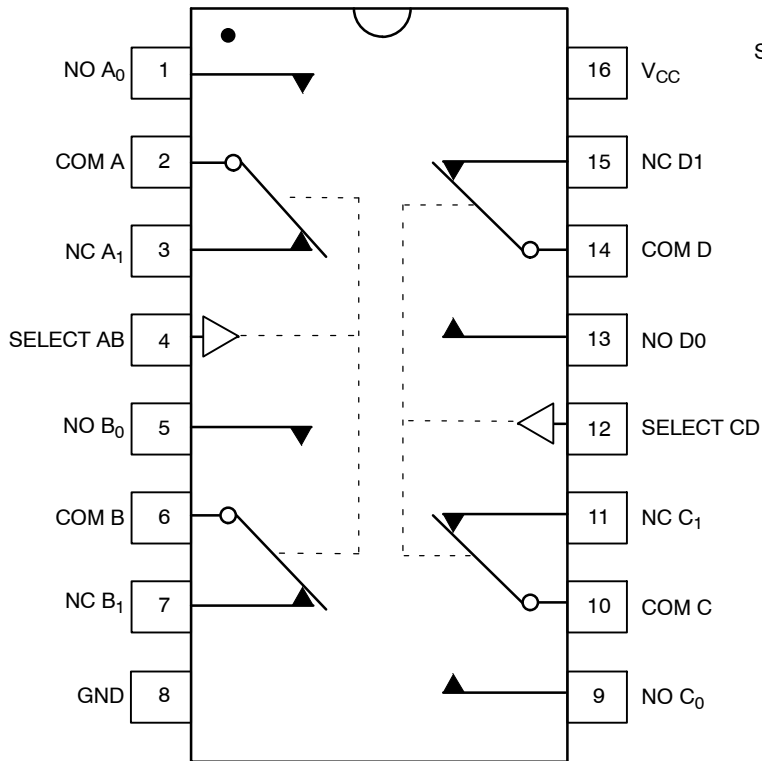
**QFN-16 PACKAGE**



**FUNCTION TABLE**

Select AB or CD	On Channel
L	NC to COM
H	NO to COM

**TSSOP-16 PACKAGE**



**Figure 2. IEC Logic Symbol**

**Figure 1. Logic Diagram**

**MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Positive DC Supply Voltage	-0.5 to +7.0	V	
V <sub>IS</sub>	Analog Input Voltage (V <sub>NO</sub> or V <sub>COM</sub> )	-0.5 ≤ V <sub>IS</sub> ≤ V <sub>CC</sub> + 0.5		
V <sub>IN</sub>	Digital Select Input Voltage	-0.5 ≤ V <sub>I</sub> ≤ +7.0	V	
I <sub>IK</sub>	DC Current, Into or Out of Any Pin	±50	mA	
P <sub>D</sub>	Power Dissipation in Still Air	QFN-16 TSSOP-16	800 450	mW
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C	
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C	
T <sub>J</sub>	Junction Temperature Under Bias	+150	°C	
MSL	Moisture Sensitivity	Level 1		
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% - 35%	UL 94-V0 (0.125 in)	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	2000 200 1000	V
I <sub>Latch-Up</sub>	Latch-Up Performance	Above V <sub>CC</sub> and Below GND at 125°C (Note 4)	±300	mA
θ <sub>JA</sub>	Thermal Resistance	QFN-16 TSSOP-16	80 164	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22-A114-A.
2. Tested to EIA/JESD22-A115-A.
3. Tested to JESD22-C101-A.
4. Tested to EIA/JESD78.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>IN</sub>	Digital Select Input Voltage	GND	5.5	V
V <sub>IS</sub>	Analog Input Voltage (NC, NO, COM)	GND	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time, SELECT	V <sub>CC</sub> = 3.3 V ± 0.3 V V <sub>CC</sub> = 5.0 V ± 0.5 V	0 100 20	ns/V

**DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES**

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

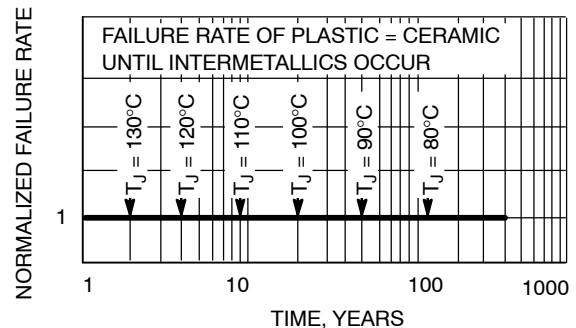


Figure 3. Failure Rate vs. Time Junction Temperature

# NLAS44599

## DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub>	Guaranteed Limit			Unit
				–55°C to 25°C	<85°C	<125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage, Select Inputs		2.0	1.5	1.5	1.5	V
			2.5	1.9	1.9	1.9	
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			5.5	3.85	3.85	3.85	
V <sub>IL</sub>	Maximum Low-Level Input Voltage, Select Inputs		2.0	0.5	0.5	0.5	V
			2.5	0.6	0.6	0.6	
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			5.5	1.65	1.65	1.65	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	5.5	±0.2	±2.0	±2.0	µA
I <sub>OFF</sub>	Power Off Leakage Current, Select Inputs	V <sub>IN</sub> = 5.5 V or GND	0	±10	±10	±10	µA
I <sub>CC</sub>	Maximum Quiescent Supply Current	Select and V <sub>IS</sub> = V <sub>CC</sub> or GND	5.5	4.0	4.0	8.0	µA

## DC ELECTRICAL CHARACTERISTICS – Analog Section

Symbol	Parameter	Condition	V <sub>CC</sub>	Guaranteed Limit			Unit
				–55°C to 25°C	<85°C	<125°C	
R <sub>ON</sub>	Maximum “ON” Resistance (Figures 17 – 23)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>IS</sub> = GND to V <sub>CC</sub>  I <sub>IN</sub>   ≤ 10.0 mA	2.5	85	95	105	Ω
			3.0	45	50	55	
			4.5	30	35	40	
			5.5	25	30	35	
R <sub>FLAT (ON)</sub>	ON Resistance Flatness (Figures 17 – 23)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub>  I <sub>IN</sub>   ≤ 10.0 mA V <sub>IS</sub> = 1 V, 2 V, 3.5 V	4.5	4	4	5	Ω
I <sub>NC(OFF)</sub> I <sub>NO(OFF)</sub>	NO or NC Off Leakage Current (Figure 9)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>NO</sub> or V <sub>NC</sub> = 1.0 V <sub>COM</sub> 4.5 V	5.5	1	10	100	nA
I <sub>COM(ON)</sub>	COM ON Leakage Current (Figure 9)	V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>NO</sub> 1.0 V or 4.5 V with V <sub>NC</sub> floating or V <sub>NO</sub> 1.0 V or 4.5 V with V <sub>NO</sub> floating V <sub>COM</sub> = 1.0 V or 4.5 V	5.5	1	10	100	nA

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r = t_f = 3.0$  ns)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	V <sub>IS</sub> (V)	Guaranteed Maximum Limit						Unit	
					-55°C to 25°C			< 85°C		< 125°C		
					Min	Typ*	Max	Min	Max	Min		Max
t <sub>ON</sub>	Turn-On Time (Figures 12 and 13)	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF (Figures 5 and 6)	2.5	2.0	5	23	35	5	38	5	41	ns
			3.0	2.0	5	16	24	5	27	5	30	
			4.5	3.0	2	11	16	2	19	2	22	
			5.5	3.0	2	9	14	2	17	2	20	
t <sub>OFF</sub>	Turn-Off Time (Figures 12 and 13)	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF (Figures 5 and 6)	2.5	2.0	1	7	12	1	15	1	18	ns
			3.0	2.0	1	5	10	1	13	1	16	
			4.5	3.0	1	4	6	1	9	1	12	
			5.5	3.0	1	3	5	1	8	1	11	
t <sub>BBM</sub>	Minimum Break-Before-Make Time	V <sub>IS</sub> = 3.0 V (Figure 4) R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	2.5	2.0	1	12		1		1		ns
			3.0	2.0	1	11		1		1		
			4.5	3.0	1	6		1		1		
			5.5	3.0	1	5		1		1		

Symbol	Parameter	Typical @ 25, V <sub>CC</sub> = 5.0 V			Unit
		Min	Typ*	Max	
C <sub>IN</sub>	Maximum Input Capacitance, Select Input		8		pF
C <sub>NO</sub> or C <sub>NC</sub>	Analog I/O (switch off)		10		
C <sub>COM</sub>	Common I/O (switch off)		10		
C <sub>(ON)</sub>	Feedthrough (switch on)		20		

\*Typical Characteristics are at 25°C.

**ADDITIONAL APPLICATION CHARACTERISTICS** (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Condition	V <sub>CC</sub> V	Typical	Unit
				25°C	
BW	Maximum On-Channel -3dB Bandwidth or Minimum Frequency Response (Figure 11)	V <sub>IN</sub> = 0 dBm V <sub>IN</sub> centered between V <sub>CC</sub> and GND (Figure 7)	3.0	145	MHz
			4.5	170	
			5.5	175	
V <sub>ONL</sub>	Maximum Feedthrough On Loss	V <sub>IN</sub> = 0 dBm @ 100 kHz to 50 MHz V <sub>IN</sub> centered between V <sub>CC</sub> and GND (Figure 7)	3.0	-3	dB
			4.5	-3	
			5.5	-3	
V <sub>ISO</sub>	Off-Channel Isolation (Figure 10)	f = 100 kHz; V <sub>IS</sub> = 1 V RMS V <sub>IN</sub> centered between V <sub>CC</sub> and GND (Figure 7)	3.0	-93	dB
			4.5	-93	
			5.5	-93	
Q	Charge Injection Select Input to Common I/O (Figure 15)	V <sub>IN</sub> = V <sub>CC</sub> to GND, F <sub>IS</sub> = 20 kHz t <sub>r</sub> = t <sub>f</sub> = 3 ns R <sub>IS</sub> = 0 Ω, C <sub>L</sub> = 1000 pF Q = C <sub>L</sub> * ΔV <sub>OUT</sub> (Figure 8)	3.0	1.5	pC
			5.5	3.0	
THD	Total Harmonic Distortion THD + Noise (Figure 14)	F <sub>IS</sub> = 20 Hz to 100 kHz, R <sub>L</sub> = R <sub>gen</sub> = 600 Ω, C <sub>L</sub> = 50 pF V <sub>IS</sub> = 5.0 V <sub>PP</sub> sine wave	5.5	0.1	%
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; V <sub>IS</sub> = 1 V RMS V <sub>IN</sub> centered between V <sub>CC</sub> and GND (Figure 7)	5.5	-90	dB
			3.0	-90	

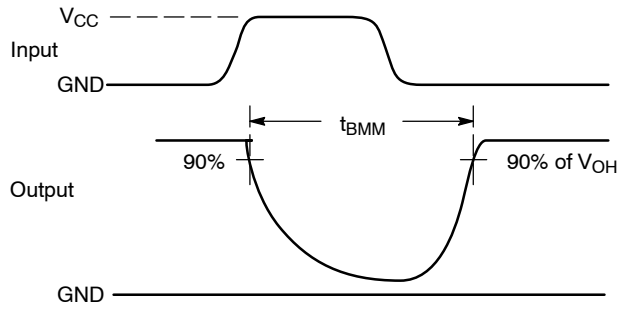
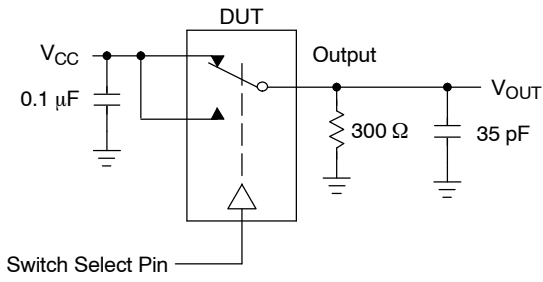


Figure 4.  $t_{BMM}$  (Time Break-Before-Make)

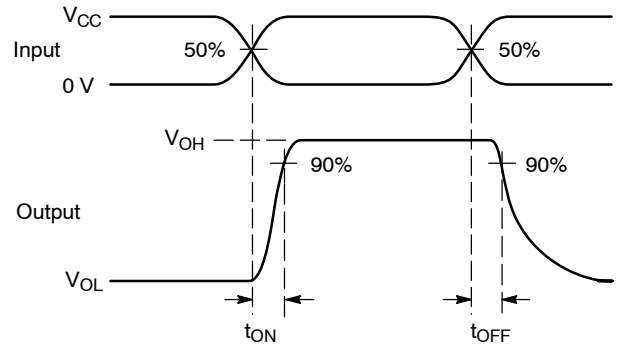
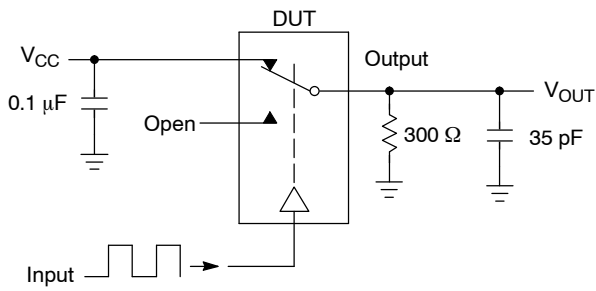


Figure 5.  $t_{ON}/t_{OFF}$

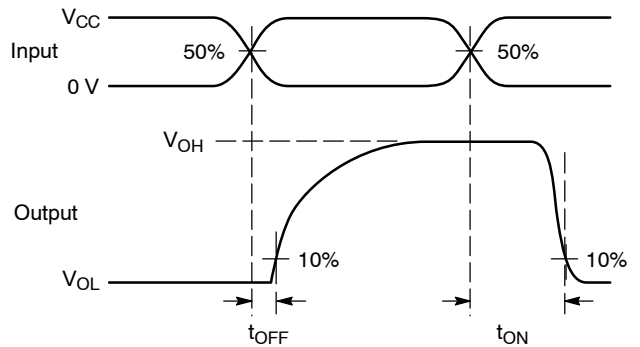
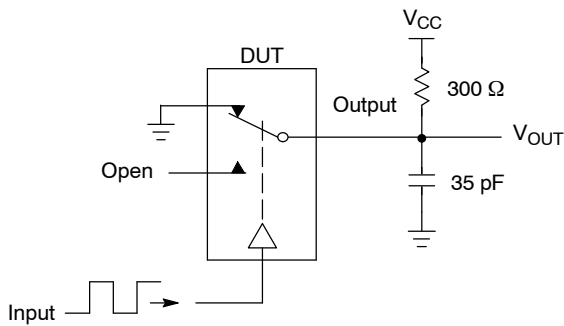
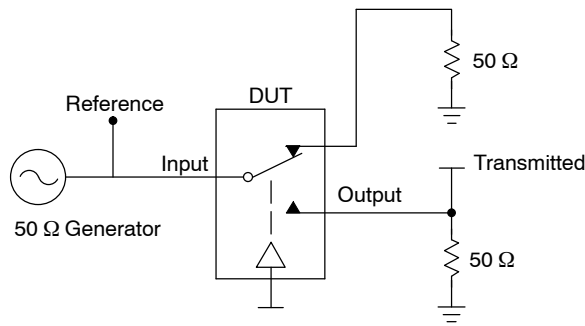


Figure 6.  $t_{ON}/t_{OFF}$



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch.  $V_{ISO}$ , Bandwidth and  $V_{ONL}$  are independent of the input signal direction.

$$V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left( \frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz}$$

$$V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left( \frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz}$$

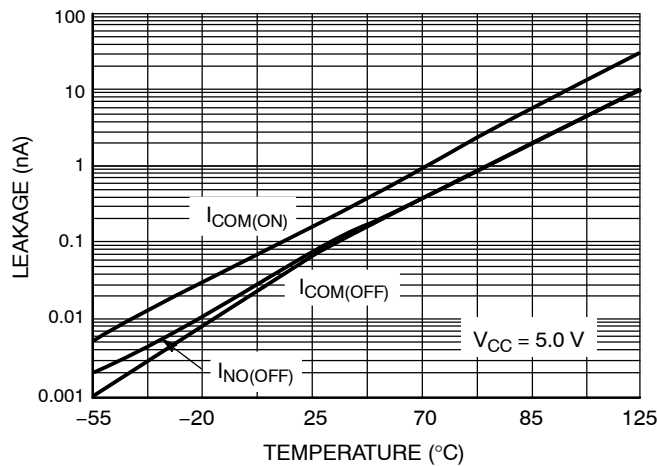
Bandwidth (BW) = the frequency 3 dB below  $V_{ONL}$

$V_{CT}$  = Use  $V_{ISO}$  setup and test to all other switch analog input/outputs terminated with 50  $\Omega$

**Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ $V_{ONL}$**



**Figure 8. Charge Injection: (Q)**



**Figure 9. Switch Leakage vs. Temperature**

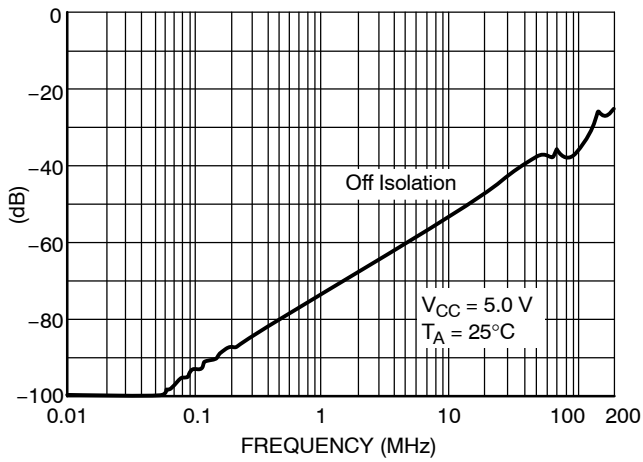


Figure 10. Off-Channel Isolation

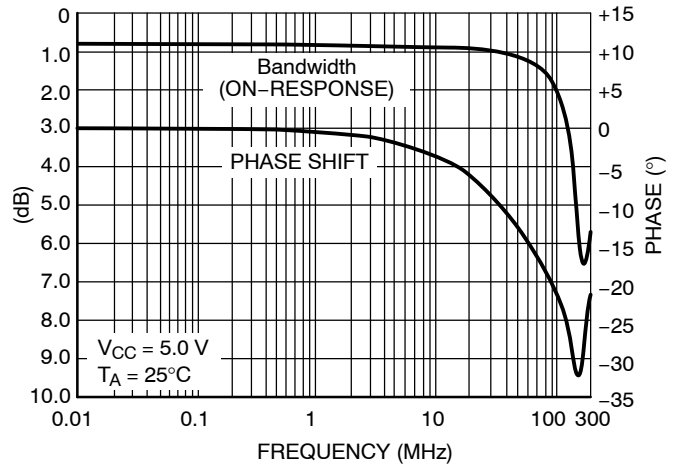


Figure 11. Typical Bandwidth and Phase Shift



Figure 12.  $t_{ON}$  and  $t_{OFF}$  vs.  $V_{CC}$  at 25°C

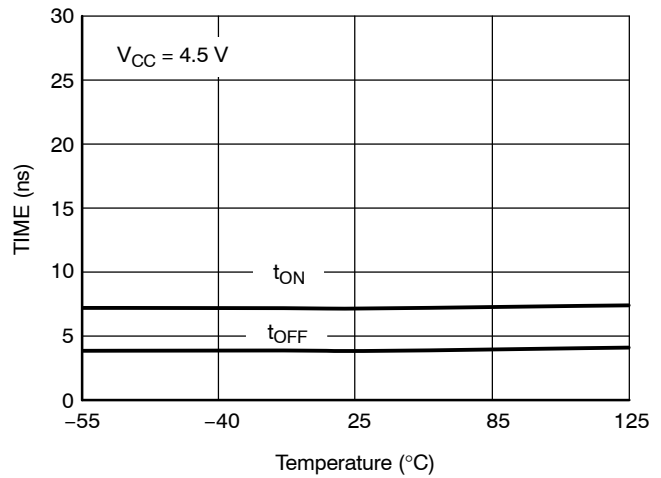


Figure 13.  $t_{ON}$  and  $t_{OFF}$  vs. Temp



Figure 14. Total Harmonic Distortion Plus Noise vs. Frequency



Figure 15. Charge Injection vs. COM Voltage





Figure 16.  $I_{CC}$  vs. Temp,  $V_{CC} = 3\text{ V}$  &  $5\text{ V}$

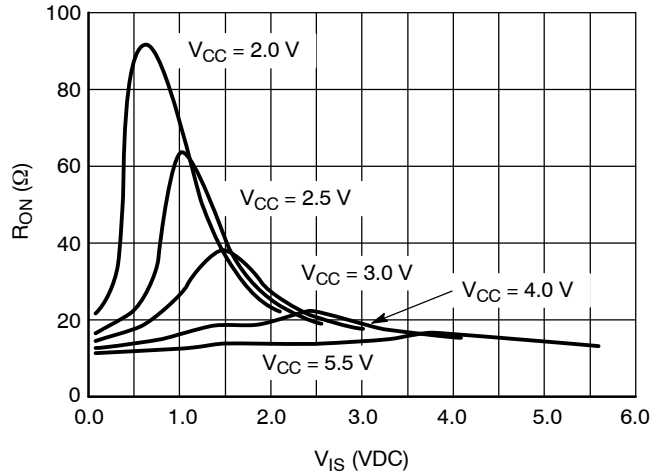


Figure 17.  $R_{ON}$  vs.  $V_{CC}$ , Temp =  $25^{\circ}\text{C}$

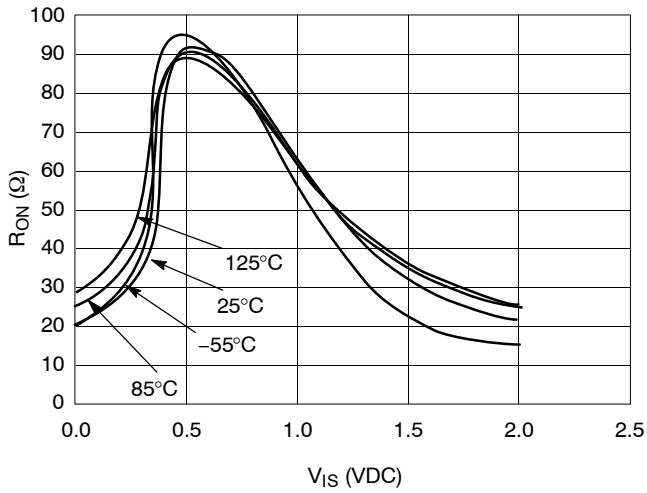


Figure 18.  $R_{ON}$  vs Temp,  $V_{CC} = 2.0\text{ V}$

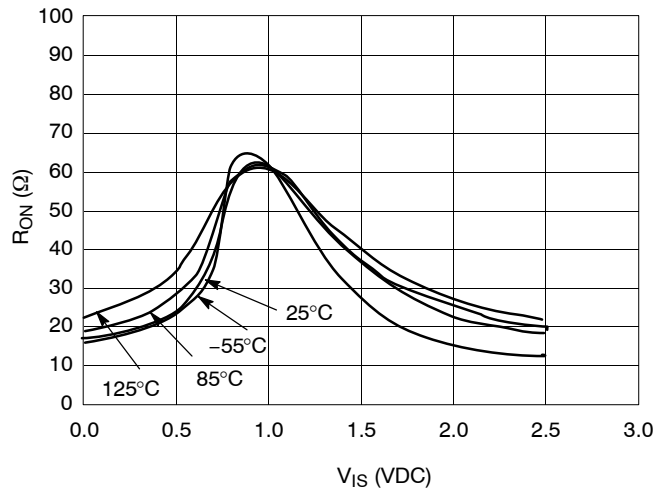


Figure 19.  $R_{ON}$  vs. Temp,  $V_{CC} = 2.5\text{ V}$

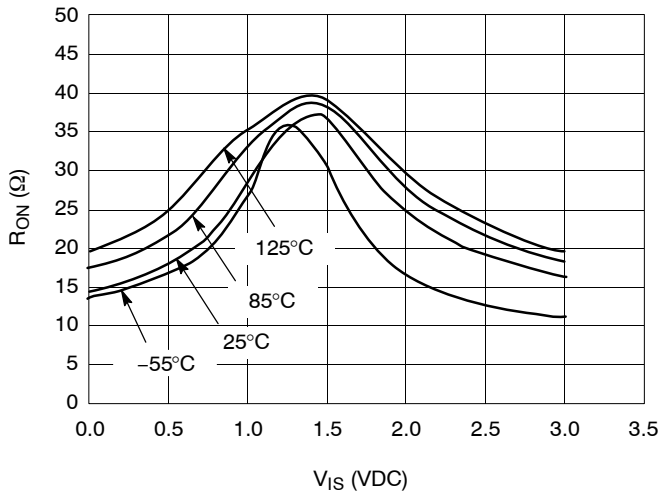


Figure 20.  $R_{ON}$  vs. Temp,  $V_{CC} = 3.0\text{ V}$

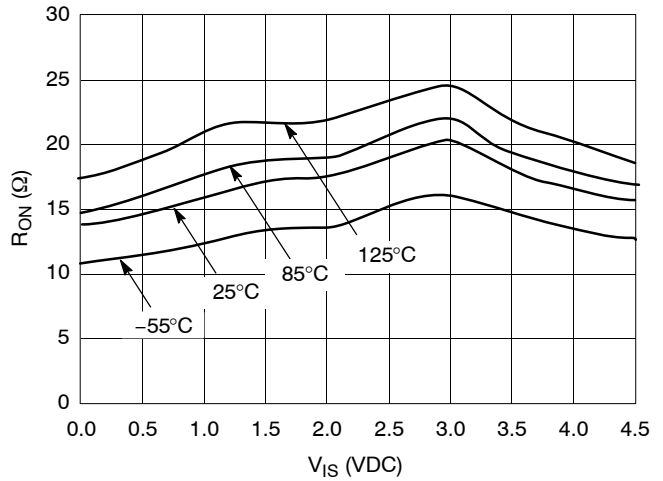


Figure 21.  $R_{ON}$  vs. Temp,  $V_{CC} = 4.5\text{ V}$

# NLAS44599



Figure 22.  $R_{ON}$  vs. Temp,  $V_{CC} = 5.0$  V

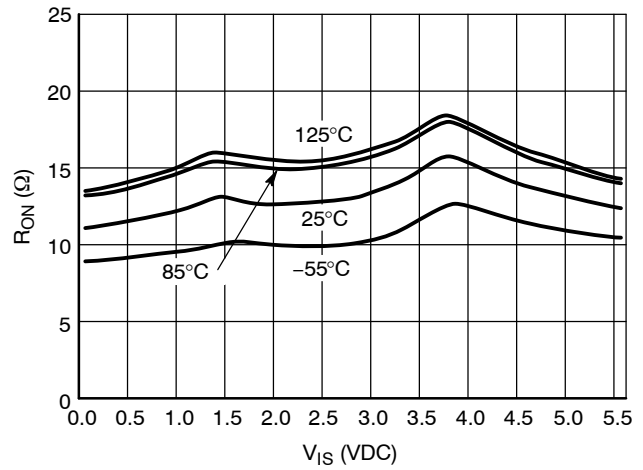


Figure 23.  $R_{ON}$  vs. Temp,  $V_{CC} = 5.5$  V

## DEVICE ORDERING INFORMATION

Device	Device Nomenclature					Package Type	Shipping <sup>†</sup>
	Circuit Indicator	Technology	Device Function	Package Suffix	Tape & Reel Suffix		
NLAS44599DT	NL	AS	44599	DT		TSSOP-16*	96 / Unit Rail
NLAS44599DTR2	NL	AS	44599	DT	R2	TSSOP-16*	2500 / Tape & Reel
NLAS44599MN	NL	AS	44599	MN		QFN-16	124 Unit / Rail
NLAS44599MNG	NL	AS	44599	MN		QFN-16 (Pb-Free)	124 Unit / Rail
NLAS44599MNR2	NL	AS	44599	MN	R2	QFN-16	2500 / Tape & Reel
NLAS44599MNR2G	NL	AS	44599	MN	R2	QFN-16 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.



1  
SCALE 2:1

QFN16 3x3, 0.5P  
CASE 485G  
ISSUE G

DATE 08 OCT 2021



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



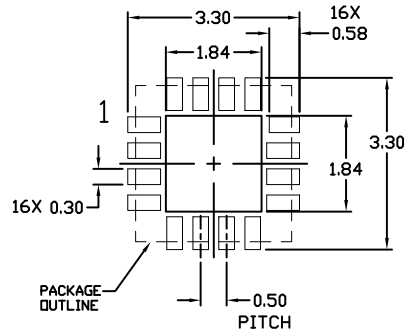
DETAIL B  
ALTERNATE  
CONSTRUCTIONS



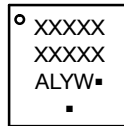
DETAIL A  
ALTERNATE TERMINAL  
CONSTRUCTIONS

DIM	MILLIMETERS		
	MIN.	NDM.	MAX.
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
A3	0.20 REF		
b	0.18	0.24	0.30
D	3.00 BSC		
D2	1.65	1.75	1.85
E	3.00 BSC		
E2	1.65	1.75	1.85
e	0.50 BSC		
k	0.18 TYP		
L	0.30	0.40	0.50
L1	0.00	0.08	0.15

MOUNTING FOOTPRINT



GENERIC MARKING DIAGRAM\*



- XXXXX = Specific Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

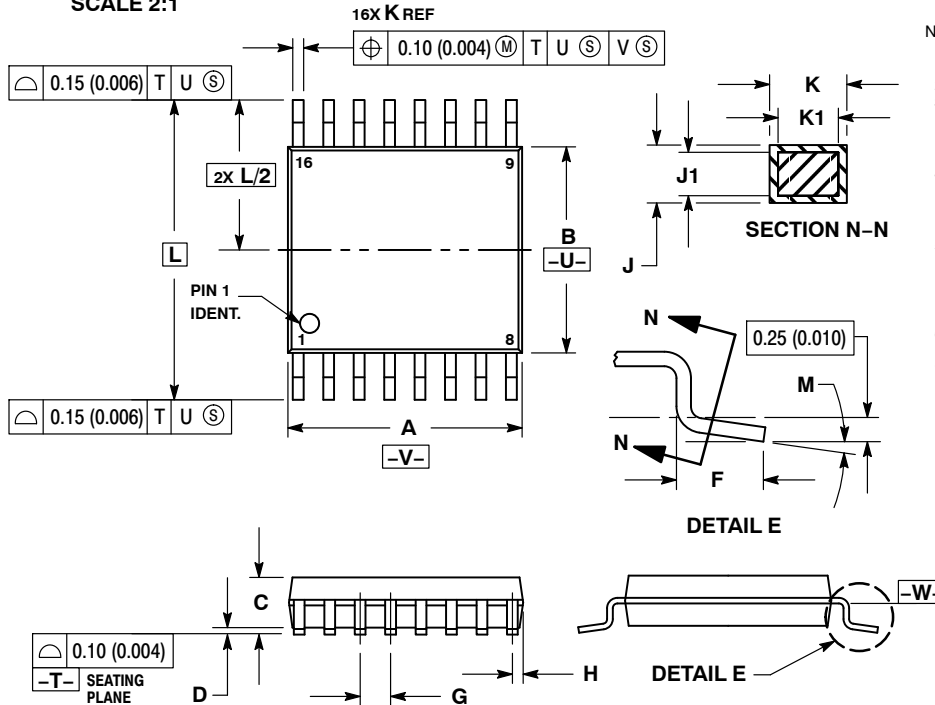
DOCUMENT NUMBER:	98AON04795D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	QFN16 3X3, 0.5P	PAGE 1 OF 1

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TSSOP-16 WB  
CASE 948F  
ISSUE B

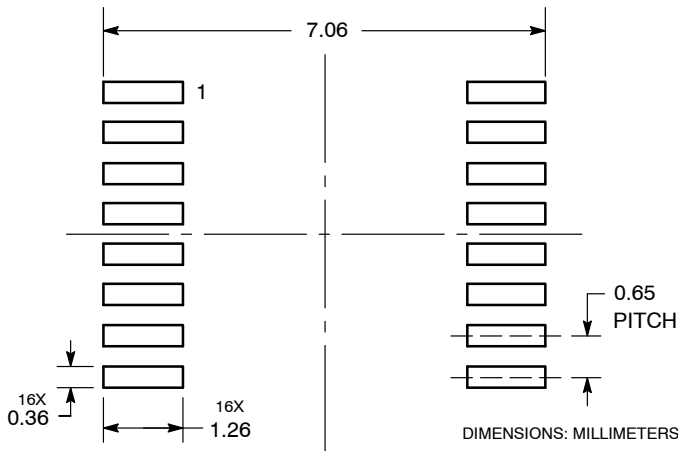
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- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

RECOMMENDED  
SOLDERING FOOTPRINT\*



GENERIC  
MARKING DIAGRAM\*



- XXXX = Specific Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- G or ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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